NSN 5962-01-335-9754

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-335-9754

Body Length:

Between 0.342 inches and 0.358 inches

Body Width:

Between 0.342 inches and 0.358 inches

Body Height:

Between 0.060 inches and 0.100 inches

Maximum Power Dissipation Rating:

303.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Burn in and bipolar and electrostatic sensitive and monolithic and programmed

Inclosure Material:

Ceramic

Inclosure Configuration:

Leadless flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

12 input

Case Outline Source And Designator:

C-2 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

50.00 nanoseconds propagation delay time, low to high level output and 50.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Pal

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 leadless

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

Yes - demil/mli

NSN 5962-01-335-9754

Memory Microcircuit - Page 2 of 2

Fiig: A458a0

